

# MAPS Geometry Simulation

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# Introduction

- We tested **Si sensitive thickness** modification.
  - Default: 0.500 mm, **MAPS: 0.015 mm (3.0%)**
  - Ecal02.cc (driver of TESLA simulation) was modified.
  - Secal01.cc (super driver of Ecal02.cc) wasn't modified. (see slides page 3,4)
  - We implemented **Non-sensitive Si volume. (0.485 mm thickness)**
  - We studied Energy deposit distribution for single electron to make comparison.

# Default Software

- Ecal02.cc (default in Mokka-05-05)
  - Si Sensitive thickness is input value from steering file.
  - Si Physical thickness is equal with Sensitive thickness.
  - Alveolus is defined with  $2 \text{ PCB} + 1 \text{ Si Sensitive}$ .
  - PCB thickness is defined in super driver SEcal01.cc as  $(\text{alveolus\_thickness} - \text{si\_thickness}) / 2$ .
  - Default values: alveolus\_thickness= 2.1 mm,  
si\_thickness= 0.5 mm,  
pcb\_thickness is not input value.

# MAPS Software Modification

- Ecal02.cc (MAPS)
  - Si Physical thickness is input from steering file.
  - Si Sensitive thickness is fixed as 0.015 mm in code.
  - Si Non-sensitive volume was implemented with (Physical\_thickness - 0.015 mm) in code.
  - Secal01.cc (super driver of Ecal02.cc) wasn't modified because still the PCB thickness definition is valid.  
$$\text{pcb\_thickness} = (\text{alveolus\_thickness} - \text{si\_thickness}) / 2.$$

Physical thickness

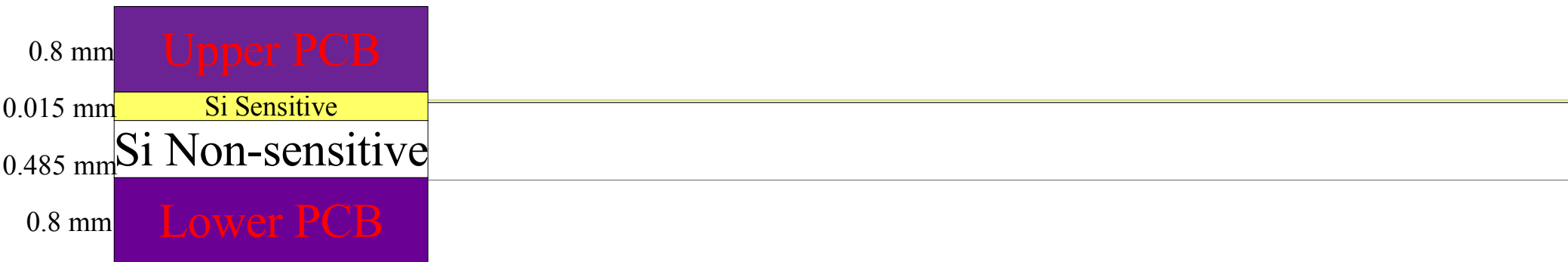


# Geometry Comparison

## Default



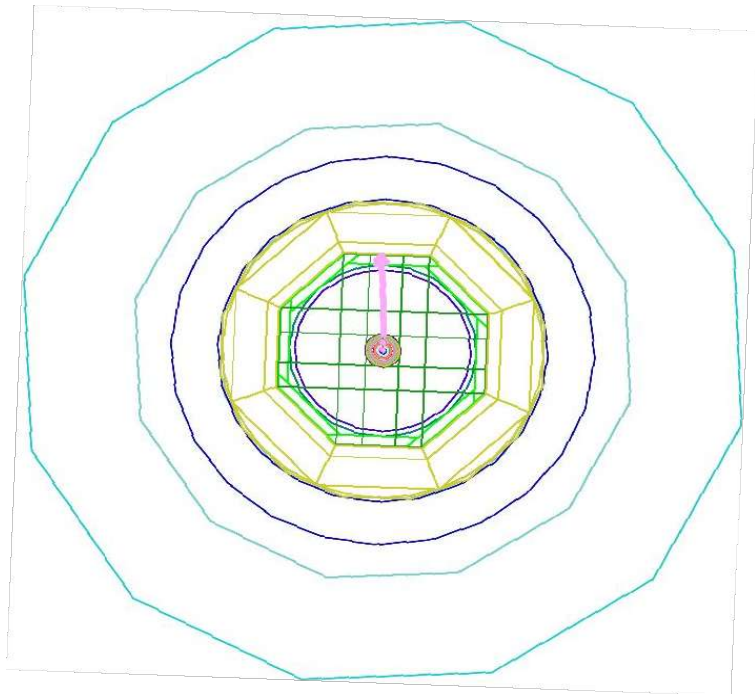
## MAPS



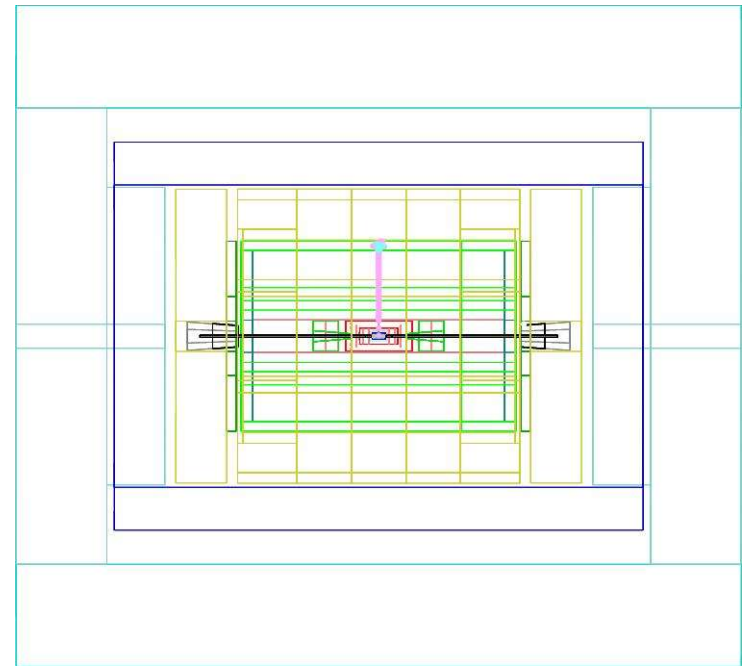
Geant4 Adaptive GUI (GAG) output distributions looks fine.

# Test Simulation Event

- We used following parameters for test simulation.
  - /gun/energy 20 GeV
  - /gun/particle e-
  - /gun/position 0 0 0
  - /gun/direction 0. 1. 0.

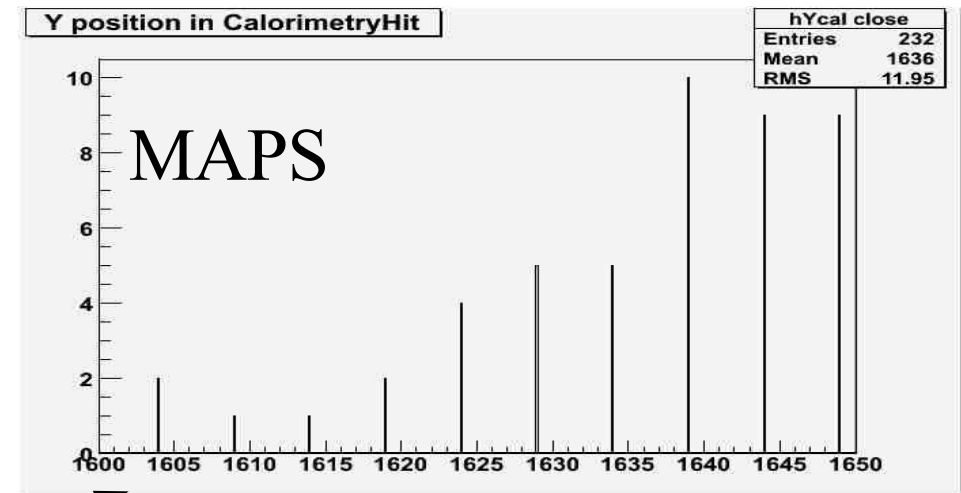
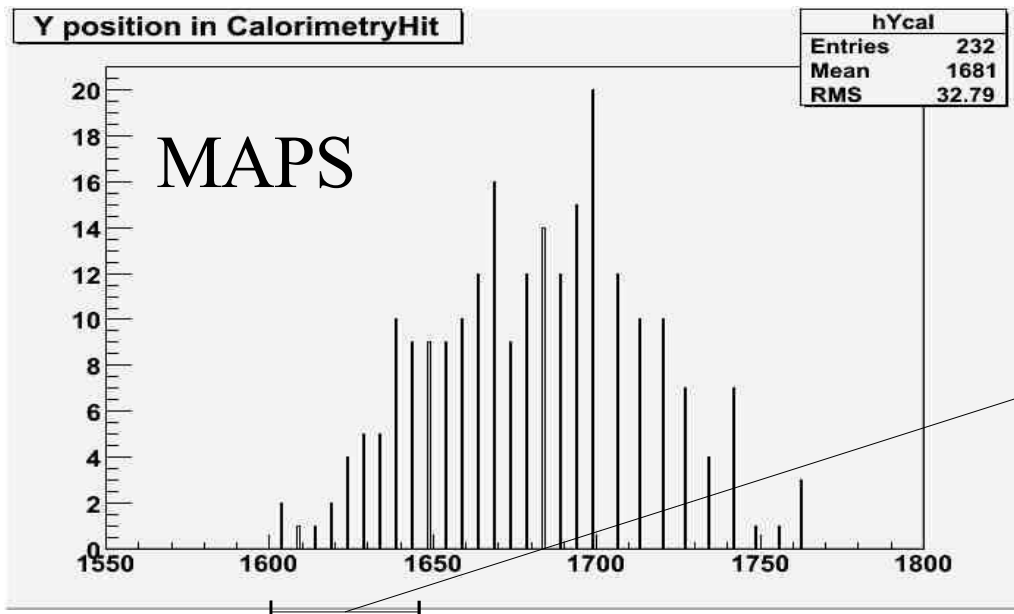
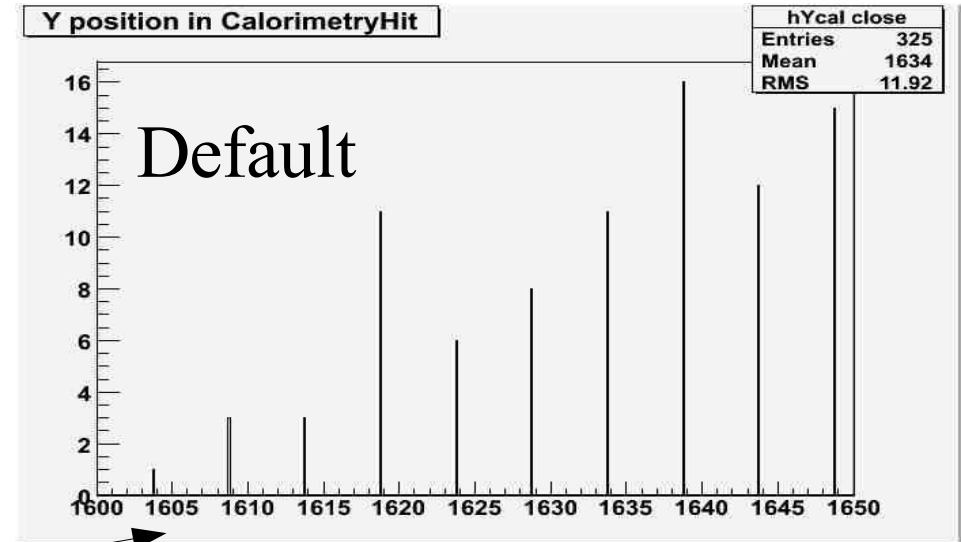
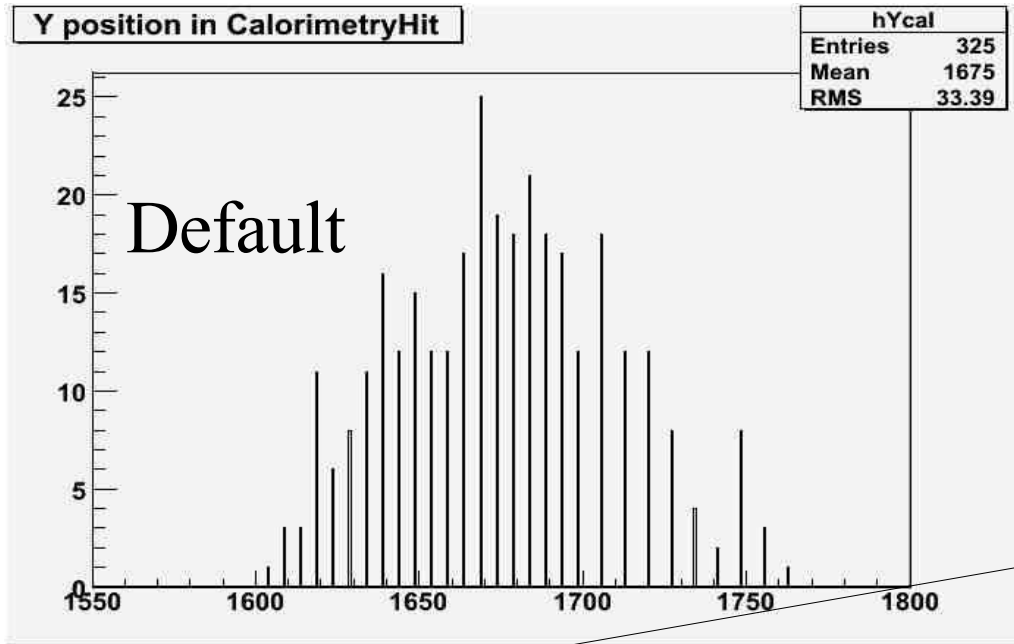


y  
↑



Only barrel top sector has hits.

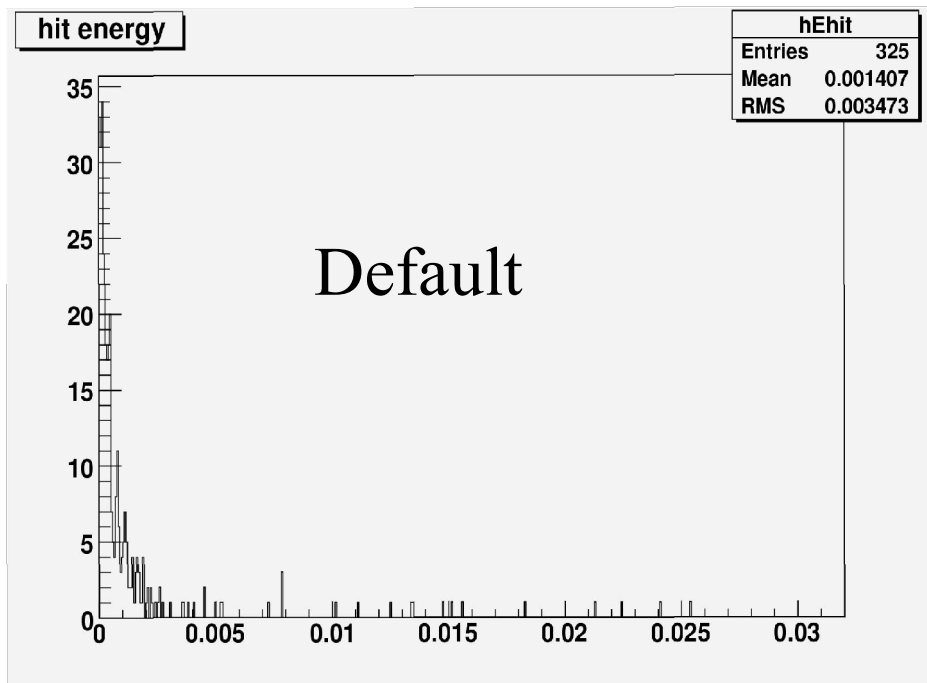
# Barrel y position distribution



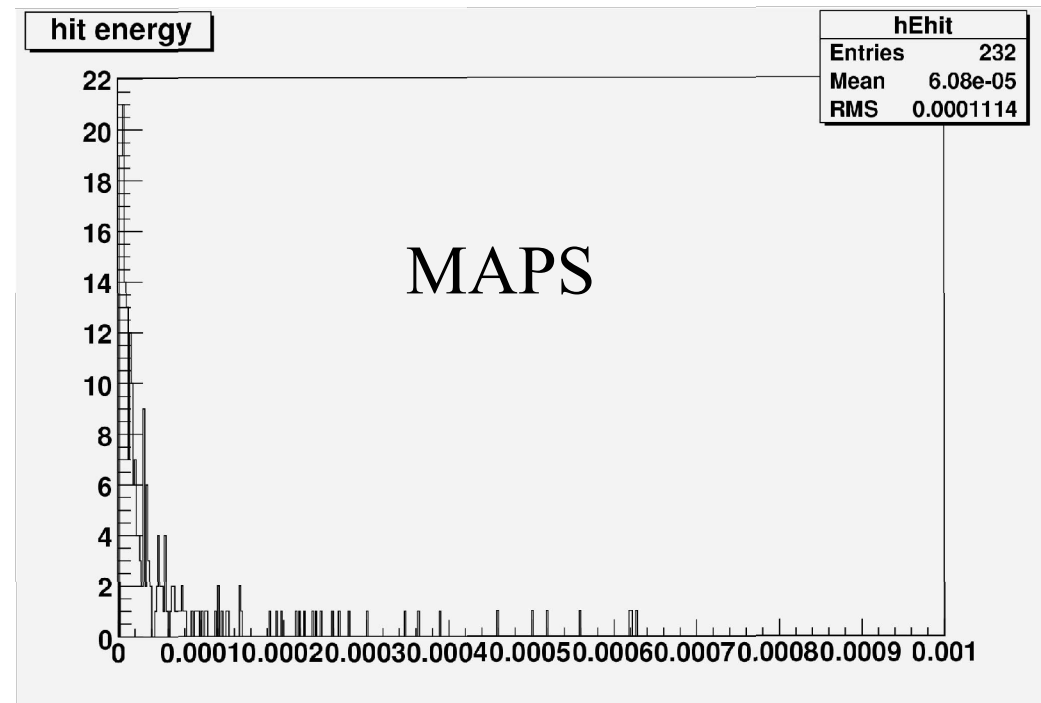
The same interval and only 0.2425 mm shifted.

# Energy Deposit Comparison

Energy deposit (Single Event)



Energy Deposit (Single Event)



Number of hits: 325  
Mean : 1.407 MeV

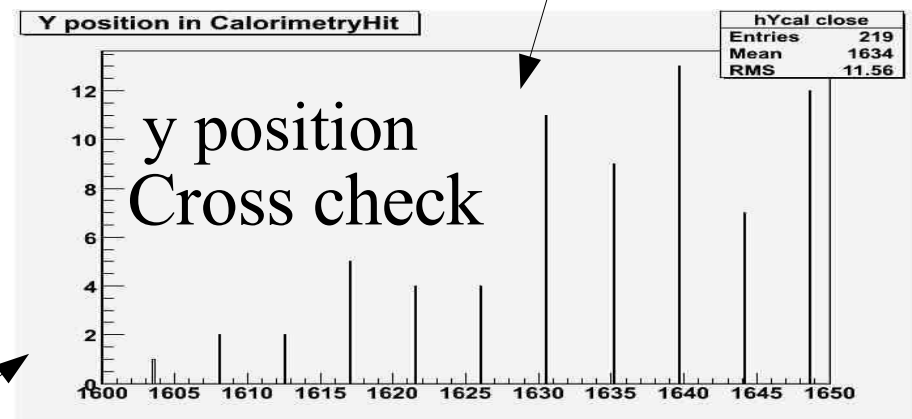
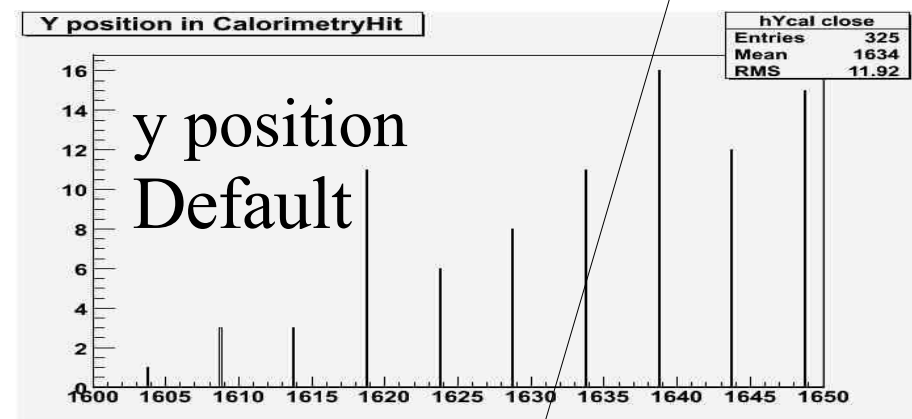
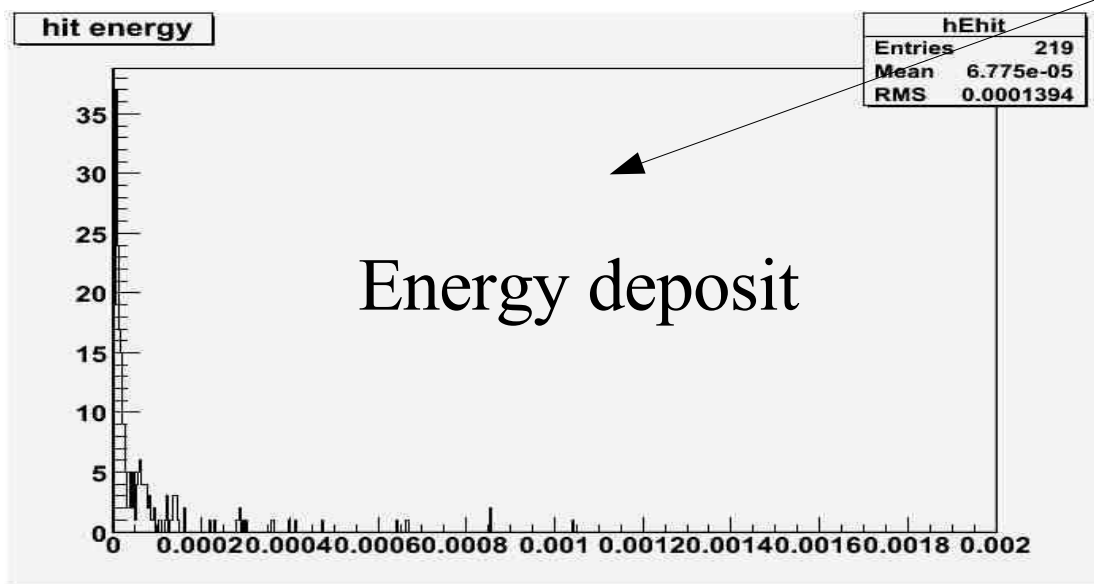
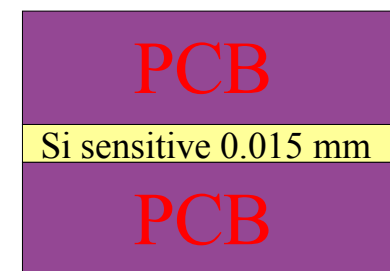
Number of hits: 232  
Mean : 60.8 KeV

Mean ratio for MAPS/Default = (4.32 +/- 0.38)%



# Consistency check (1)

- We tested **0.015 mm Si sensitive** without any **Non-sensitive Si volume**.



Number of hits : 219

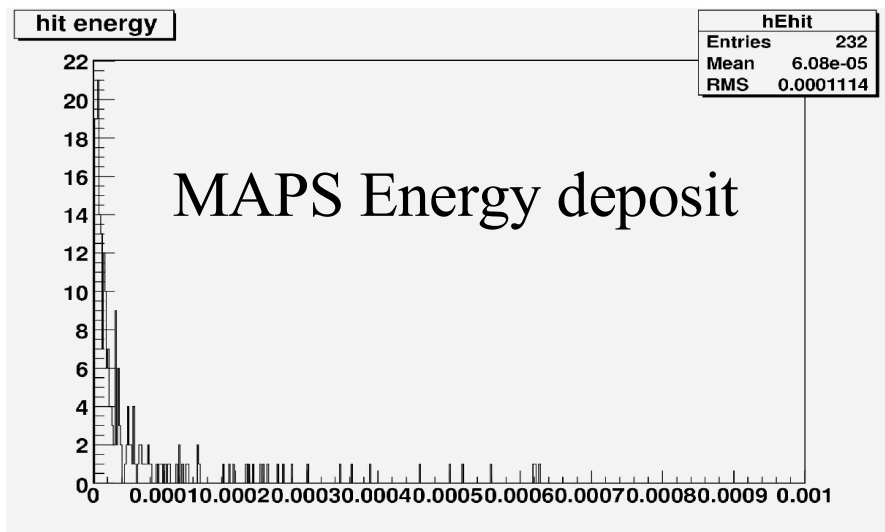
Mean : 67.8 KeV

Similar with MAPS modification.

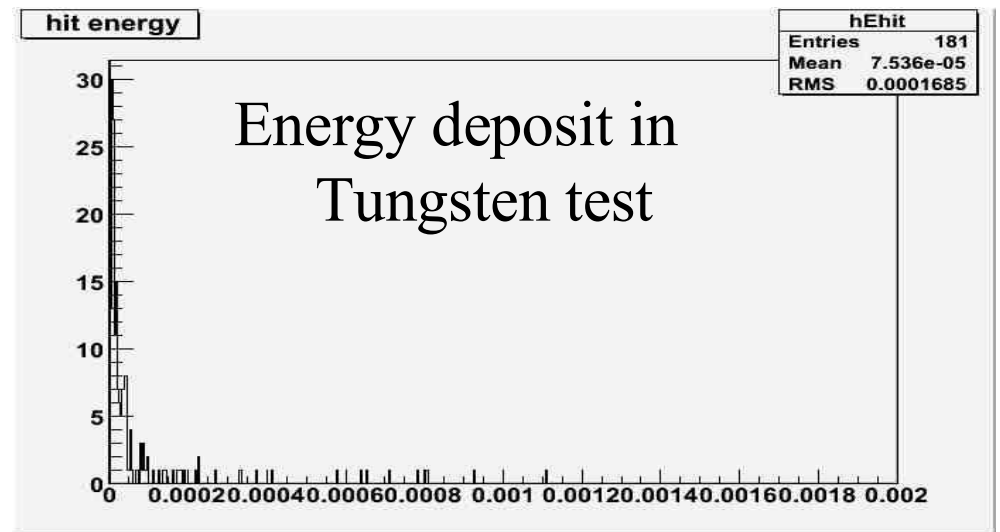
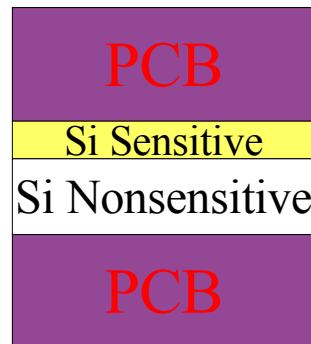
Interval is 0.485 mm smaller than default.

# Consistency Check (2)

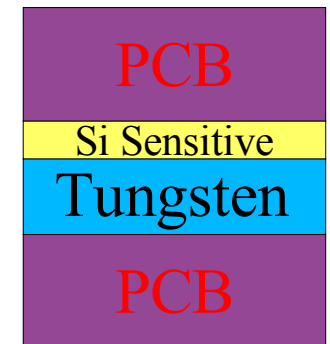
- We tested implement of Tungsten instead of Silicon-Non-Sensitive volume for cross check.



Number of Hits: 232  
Mean of Hits: 60.8 KeV

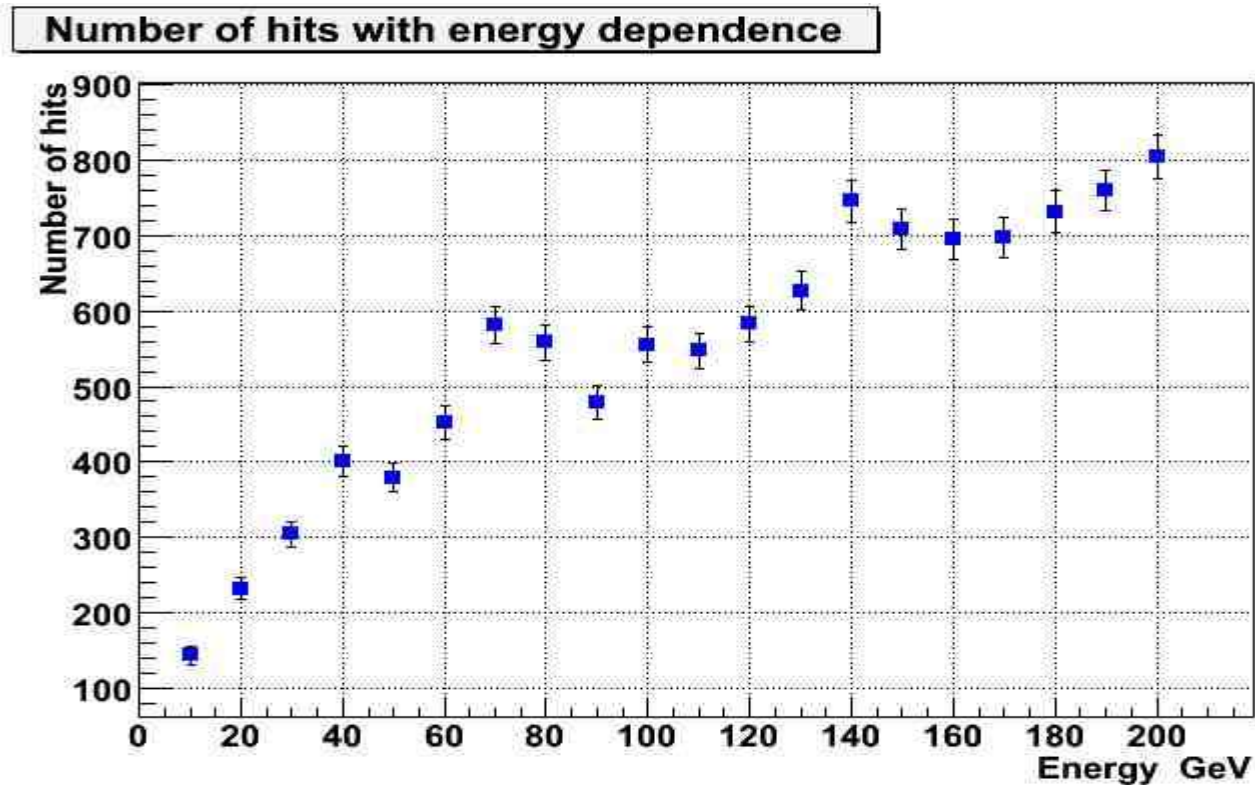


Number of Hits: 181  
Mean of Hits: 75.4 KeV



# Energy Dependence for Number of Hits

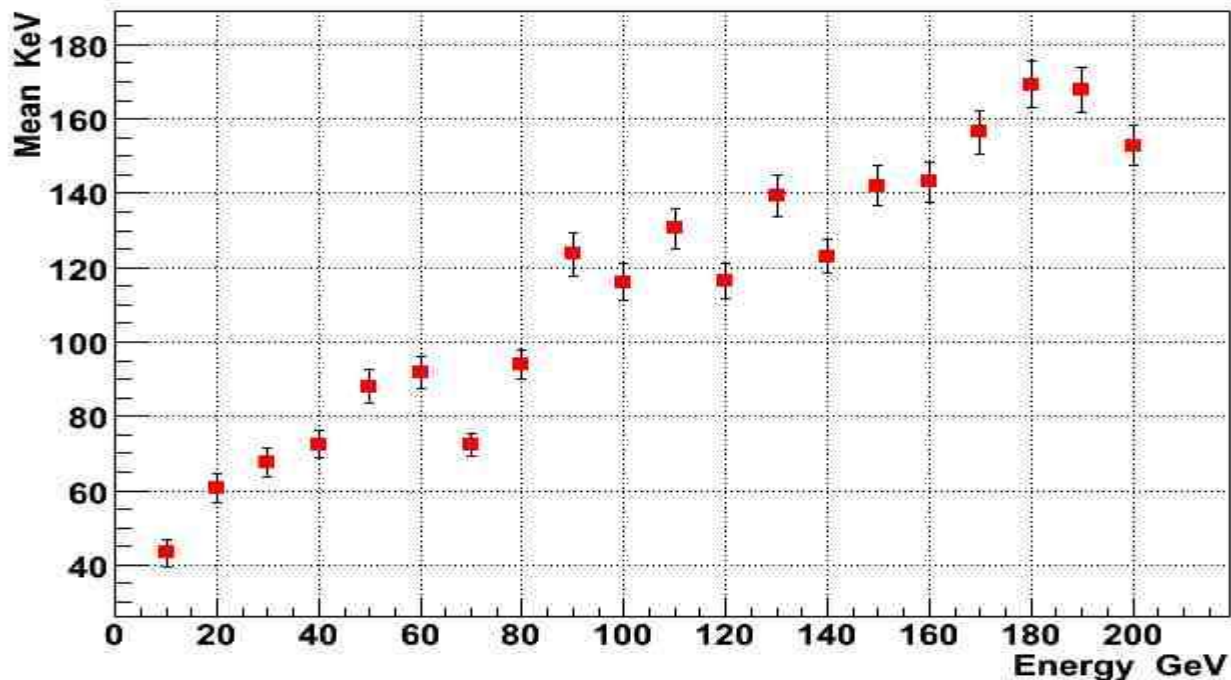
- Single electron event
- Si Sensitive thickness is 0.015 mm
- Si Non-sensitive thickness is 0.485 mm
- Cell size is still 1 cm times 1 cm



# Mean of Hits Energy with Energy Dependence

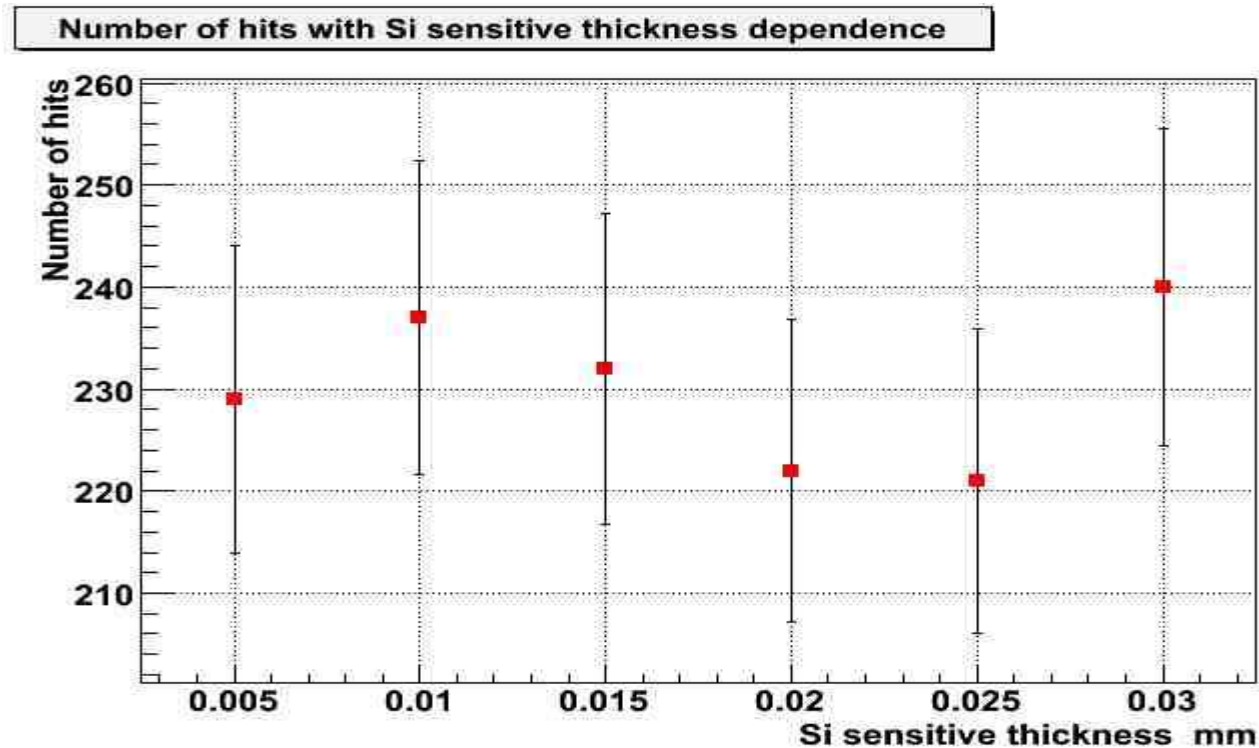
- Single electron event
- Si Sensitive thickness is 0.015 mm
- Si Non-sensitive thickness is 0.485 mm
- Cell size is still 1cm times 1cm

Mean of hits with energy dependence



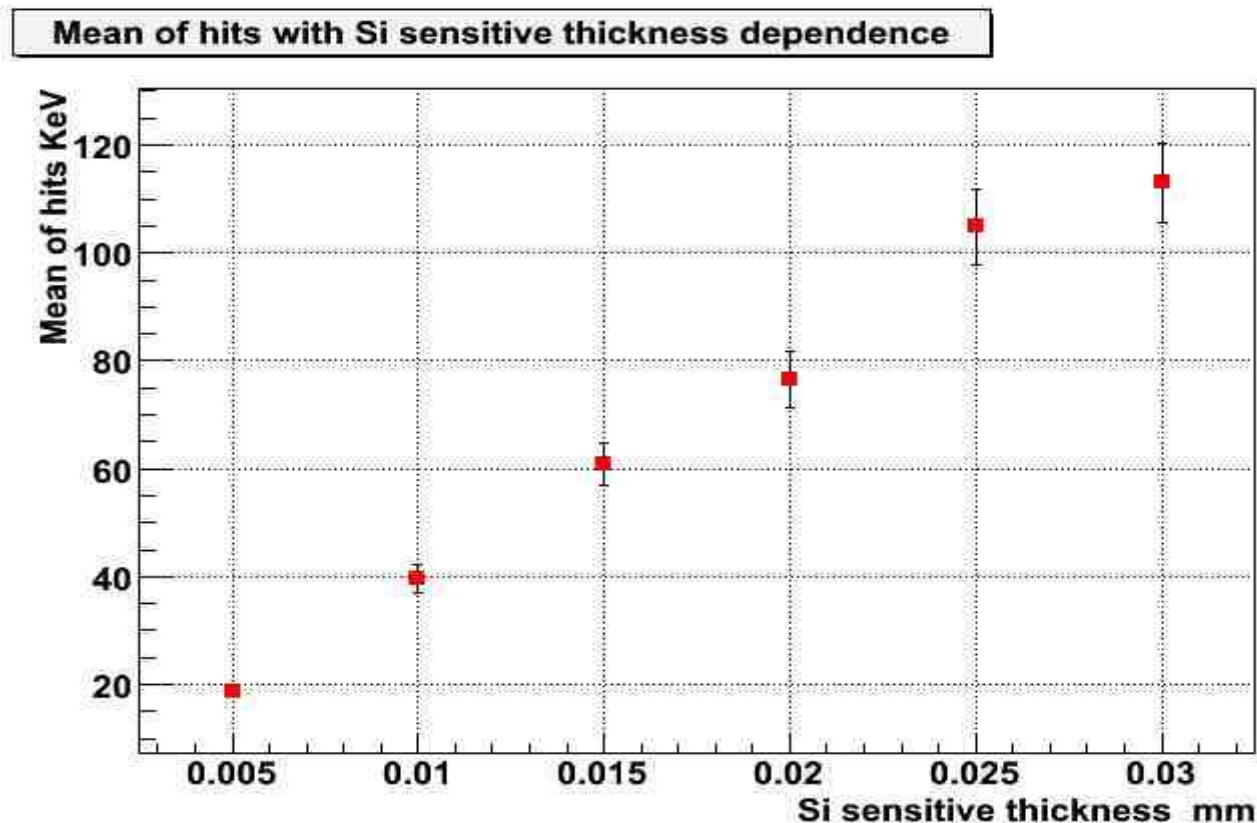
# Number of Hits with Si Sensitive Thickness dependence

- 20 GeV single electron event
- Si Physical thickness is 0.500 mm
- Cell size is still 1cm times 1cm



# Mean of Hits with Si Sensitive Thickness Dependence

- 20 GeV single electron event
- Si Physical thickness is 0.500 mm
- Cell size is still 1cm times 1cm



# Summary and Next Steps

- Summary
  - We studied Si thickness modification. (Mokka-05-05 Geant4-8 and LCIO-v01-06 are used.)
  - The modification looks working well.
- Next steps
  - More statistics
  - Cell size changes
  - Digitization for position
  - Energy/angle/position resolutions
  - Systematic studies and cross checks